



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

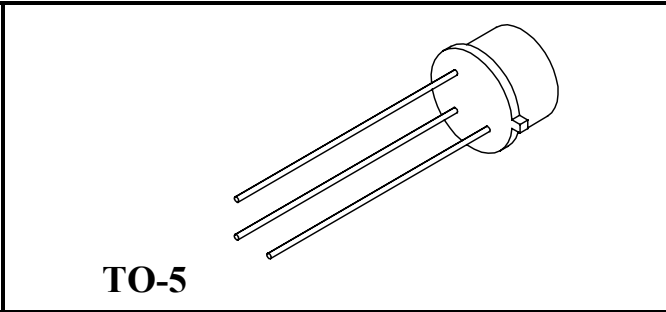
**SSR1008/5
SSR1009/5
SSR1010/5**

**10 AMP
80 – 100 VOLTS
SCHOTTKY RECTIFIER**

Designer's Data Sheet

FEATURES:

- **Extremely Low Forward Voltage Drop**
- **Low Reverse Leakage**
- **Hermetically Sealed Package**
- **Guard Ring for Overvoltage Protection**
- **Eutectic Die Attach**
- **175°C Operating Junction Temperature**
- **TX, TXV, or Space Level Screening Available**



MAXIMUM RATINGS

| RATING | SYMBOL | VALUE | UNIT |
|--|---|--|--------------|
| Peak Repetitive Reverse Voltage and DC Blocking Voltage SSR1008/5 SSR1009/5 SSR1010/5 | V_{RRM} V_{RWM} V_R | 80 90 100 | Volts |
| Average Rectified Output Current ^{1/} (Resistive Load, 60Hz, Sine Wave, TA=25°C) | I_O | 10 | Amps |
| Peak Surge Current ^{1/} (8.3 ms Pulse, Half Sine Wave, superimposed on I_O , allow junction to reach equilibrium between pulses, TA=25°C) | I_{FSM} | 150 | Amps |
| Operating and Storage Temperature | $T_{OP} \& T_{STG}$ | -65 to +175 | °C |
| Maximum Thermal Resistance ^{1/} Junction to Case | $R_{\theta JC}$ | 7.0 | °C/W |

Notes: ^{1/} For optimal performance, connect leads 1 & 2 together (Anode).



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ELECTRICAL CHARACTERISTICS

| CHARACTERISTICS | SYMBOL | MAXIMUM | UNIT |
|--|---|----------------------|------|
| Instantaneous Forward Voltage Drop ^{2/} (I _F = 1 Adc, T _A = 25°C, 300 - 500µs Pulse) (I _F = 5 Adc, T _A = 25°C, 300 - 500µs Pulse) (I _F = 10 Adc, T _A = 25°C, 300 - 500µs Pulse) | V _{F1} V _{F2} V _{F3} | 0.56 0.73 0.85 | Vdc |
| Instantaneous Forward Voltage Drop (I _F = 5 Adc, T _A = -55°C, 300 - 500µs Pulse) | V _{F4} | 0.82 | Vdc |
| Reverse Leakage Current (Rated V _R , T _A = 25°C, 300µs Pulse Minimum) | I _{R1} | 100 | µA |
| Reverse Leakage Current (Rated V _R , T _A = 100°C, 300µs Pulse Minimum) | I _{R2} | 5 | mA |
| Junction Capacitance (V _R = 10 Vdc, T _A = 25°C, f = 1 MHz) | C _J | 400 | pF |

NOTES:

^{2/} V_F as measured between pins 1 and 2 in common, within .100" from the case, and pin 3 directly at the case.

